



JX040 Series Sensitive gate SCRs

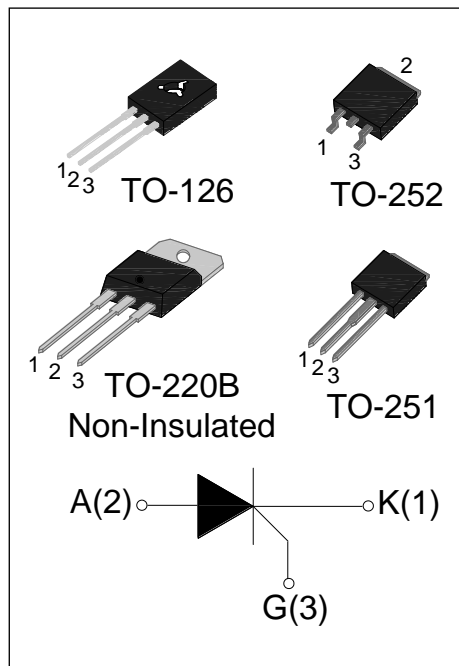
Rev.4.0

DESCRIPTION:

The JX040 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.

MAIN FEATURES

Symbol	Value	Unit
V_{DRM}/V_{RRM}	600	V
$I_{T(RMS)}$	4	A
I_{GT}	≤200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 110	°C
Repetitive peak off-state voltage		V_{DRM}	600	V
Repetitive peak reverse voltage		V_{RRM}	600	V
RMS on-state current	TO-126 ($T_C=85^\circ\text{C}$)	$I_{T(RMS)}$	4	A
	TO-251/ TO-252 ($T_C=90^\circ\text{C}$)			
	TO-220B(Non-Ins) ($T_C=97^\circ\text{C}$)			
Non repetitive surge peak on-state current (tp=10ms)		I_{TSM}	30	A
I^2t value for fusing (tp=10ms)		I^2t	4.5	A^2s
Critical rate of rise of on-state current		di/dt	50	$A/\mu s$
Peak gate current (tp=20μs, $T_j=110^\circ\text{C}$)		I_{GM}	1.2	A
Peak gate power (tp=20μs, $T_j=110^\circ\text{C}$)		P_{GM}	2	W
Average gate power dissipation($T_j=110^\circ\text{C}$)		$P_{G(AV)}$	0.2	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=110^{\circ}\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05\text{A}$	-	-	5	mA
dV/dt	$V_D=2/3V_{DRM} T_j=110^{\circ}\text{C} R_{GK}=1\text{K}\Omega$	10	-	-	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_T=8\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=110^{\circ}\text{C}$	100	μA

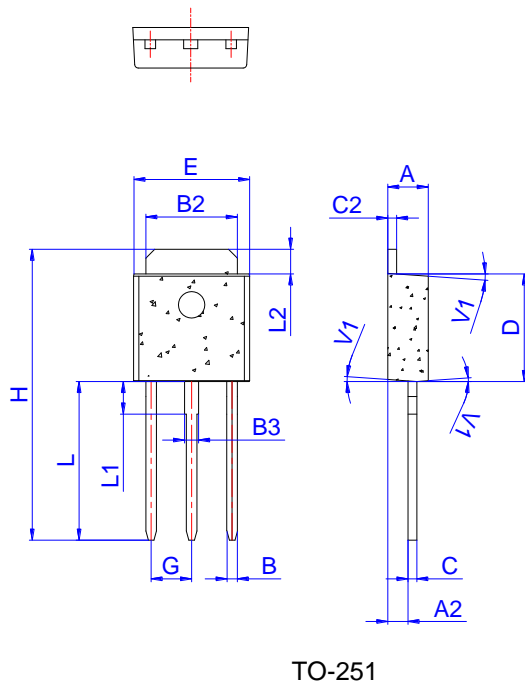
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-126	7.2	$^{\circ}\text{C/W}$
		TO-251/ TO-252	6.5	
		TO-220B(Non-Ins)	3.0	

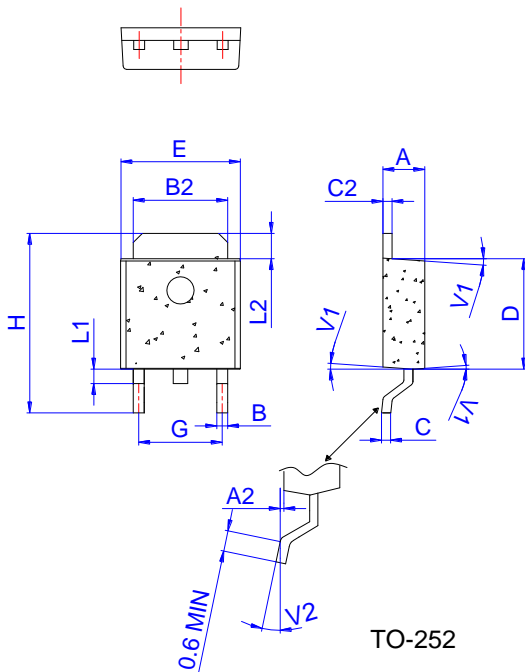
ORDERING INFORMATION

J JieJie Microelectronics Co.,Ltd Sensitive gate SCRs	X $I_{T(RMS)}:4\text{A}$	040	H Q:TO-126 B:TO-220B(Non-Ins) H:TO-251 K:TO-252
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PACKAGE MECHANICAL DATA

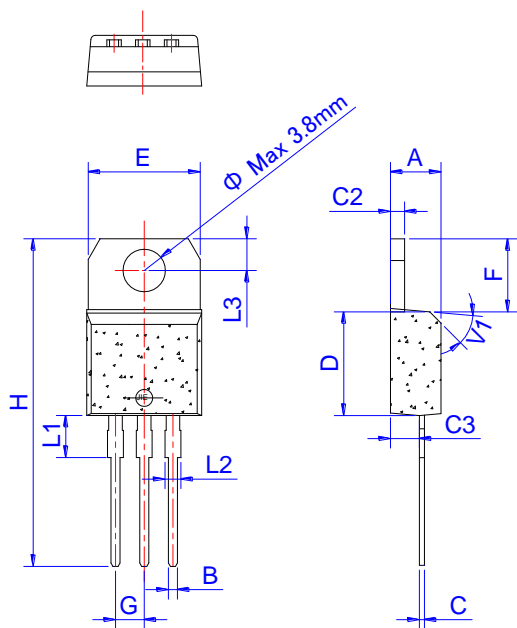


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



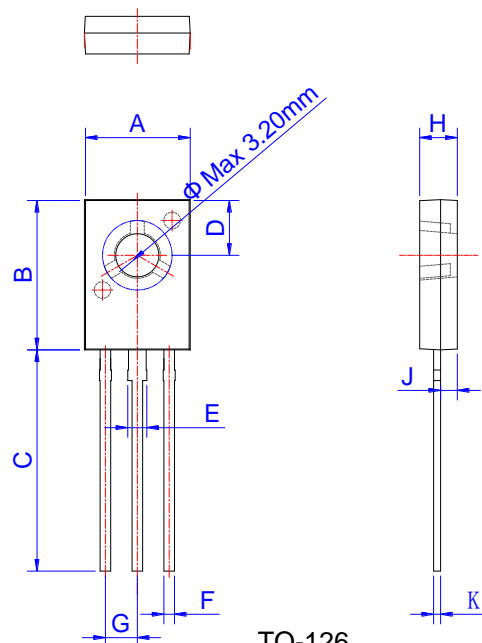
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2		0°	8°		0°	8°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-126

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

FIG.1: Maximum power dissipation versus RMS on-state current

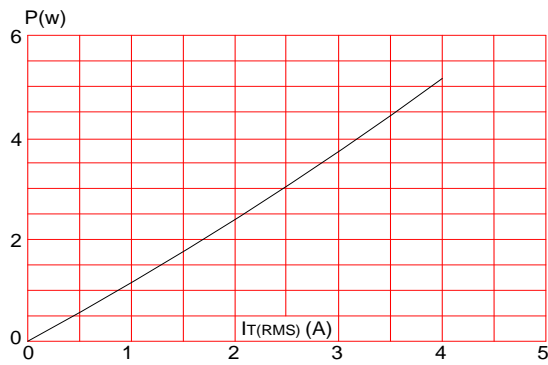


FIG.3: Surge peak on-state current versus number of cycles

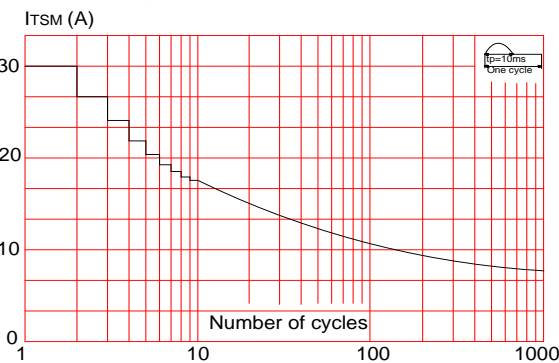


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

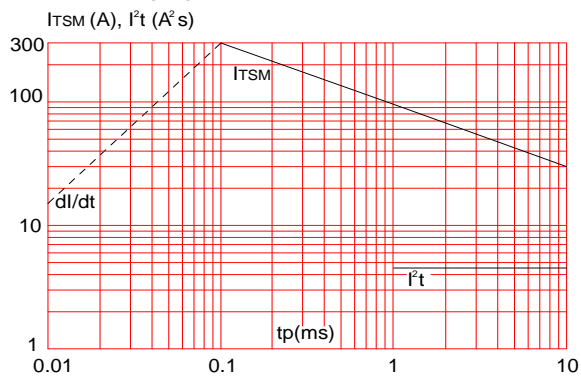


FIG.2: RMS on-state current versus case temperature

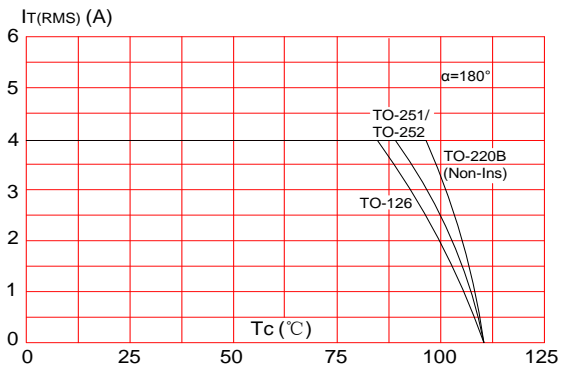


FIG.4: On-state characteristics (maximum values)

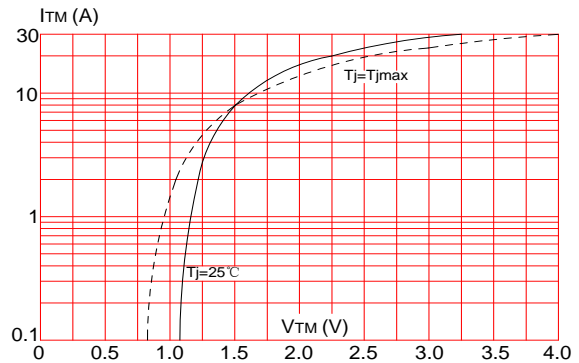
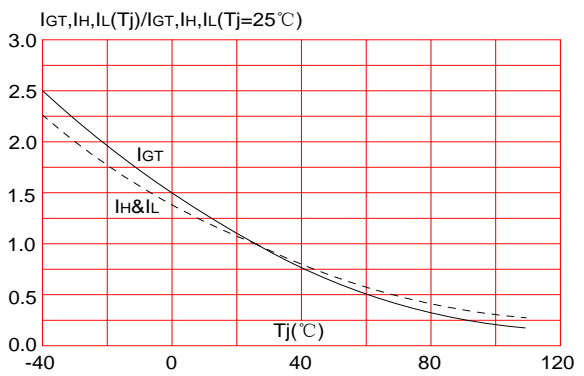



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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